



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#12/Amdt A
10/9/02
C. Davis

Patent Application No. 09/833,078)	Art Unit 2814
)	
Filed April 12, 2001)	Examiner: W. Louie
)	
Confirmation No. 1456)	Attorney Docket No.:
)	115354-00116
Inventors: David A. THOMPSON et al)	(formerly 45-35)
)	
For: METHOD FOR LOCALLY MODIFYING)	
THE EFFECTIVE BANDGAP ENERGY)	
IN INDIUM GALLIUM ARSENIDE)	
PHOSPHIDE (InGaAsP) QUANTUM)	
WELL STRUCTURES)	October 3, 2002

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AMENDMENT

Hon Commissioner for Patents
Box Non-Fee Amendment
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 3, 2002, please amend the above-captioned patent application as follows:

In the claims:

Kindly cancel claims 17-~~21~~ without prejudice to the subject matter thereof.

Please add the following new claims:

AI --22. (New) A method as defined in claim 14, wherein the reduced temperature MBE process is performed at a temperature of 300°C.

23. (New) A method as defined in claim 15, wherein the thickness of the grown Indium Phosphide layer is not greater than 1000Å.

24. (New) A method as defined in claim 1, wherein the first Indium Phosphide layer has a thickness not greater than 400Å.--